

Form PTO-1449  <b>INFORMATION DISCLOSURE CITATION IN AN APPLICATION</b>  (Use several sheets if necessary)	ATTY DOCKET NO. 04202	APPLICATION NO. 10/512,077
	APPLICANT Olivier Marty et al.	
	FILING DATE November 5, 2004	GROUP

## U.S. PATENT DOCUMENTS

[illegible]

## FOREIGN PATENT DOCUMENTS

[illegible]

**OTHER DOCUMENTS** (Including Author, Title, Date, Pertinent Pages, etc.)

GWR	Romanov et al, "GeSi Films With Reduced Dislocation Density Grown by Molecular-Beam Epitaxy on compliant Substrates Based on Porous Silicon" Applied Physics Letter, etc., Vol. 75, No. 26, Dec. 27, 1999, pp 4118-4120.
GWR	Sanchez et al, "Structural and Morphological Characteristics of InGaAs/GaAs Quantum Well Structures on Tilted (111)BGaAs Grown by MBE", Journal of Crystal Growth etc., Vol. 192, No. 3-4, Sept. 1, 1998, pp 363-371.

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.